

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
FETHE24.001CP1APPLICATION NO.
10/005,186INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANTS
Camm, et al.FILING DATE
December 4, 2001GROUP ART UNIT
3742

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TECHNOLOGY CENTER R3700

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
STJ	1,587,023	06/01/26	Mottlau			
	24,296 RE	03/26/57	Stewart			
	2,981,819	04/25/61	Gregory			
	3,047,438	07/31/62	Marinace			
	3,108,713	10/22/63	Barrett, et al.			
	3,160,517	12/08/64	Jenkin			
	3,188,459	06/08/65	Bridwell			
	3,227,065	01/04/66	Litman			
	3,239,651	03/08/66	Silberman			
	3,240,915	03/15/66	Carter, et al.			
	3,460,510	08/12/69	Currin			
	3,502,516	03/24/70	Henker			
	3,623,712	11/30/71	McNeilly, et al.			
	3,627,590	12/14/71	Mammel			
	3,661,637	04/09/72	Sirtl			
	3,692,572	09/19/72	Strehlow			
	3,836,751	09/17/74	Anderson			
	3,913,872	10/21/75	Weber			
	4,041,278	08/09/77	Boah			
	4,081,313	03/28/78	McNeille, et al.			
	4,097,226	06/27/78	Erikson, et al.			
	4,101,759	07/18/78	Anthony, et al.			
	4,115,163	09/19/78	Gorina, et al.			
	4,151,008	04/24/79	Kirkpatrick			
	4,164,643	08/14/79	Peart, et al.			
	4,220,483	09/02/80	Cazcarra			
	4,224,096	09/23/80	Osborne			

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Shawntina Fugua

DATE CONSIDERED

3/7/04

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANTS Cam, et al.	
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U.S. PATENT DOCUMENTS

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	4,233,493	11/11/80	Nath			
	4,308,078	12/29/81	Cook			
	4,315,130	02/09/82	Inagaki, et al.			
	4,331,485	05/25/82	Gat			
	4,370,175	01/25/83	Levatter			
	4,375,993	03/08/83	Mori, et al.			
	4,379,727	04/12/83	Hansen, et al.			
	4,398,094	08/9/83	Hiramoto			
	4,421,048	12/20/83	Adema, et al.			
	4,431,459	02/14/84	Teng			
	4,455,479	06/19/84	Itoh, et al.			
	4,493,977	01/15/85	Arai, et al.			
	4,533,820	08/06/85	Shimizu			
	4,539,431	09/03/85	Moddel, et al.			
	4,540,876	09/10/85	McGinty			
	4,550,245	10/29/85	Arai, et al.			
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	4,567,352	01/28/86	Mimura, et al.			
	4,649,261	03/10/87	Sheets			
	4,680,447	07/14/87	Mahawili			
	4,698,486	10/06/87	Sheets			
	5,219,786	06/15/93	Noguchi			
	5,336,641	08/09/94	Fair, et al.			
	5,399,506	03/21/95	Tsukamoto			
	5,446,825	08/29/95	Moslehi, et al.			
	5,908,307	06/01/99	Talwar, et al.			
	6,051,483	04/18/00	Lee, et al.			

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANTS Camm, et al.	
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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Sf	32864	08/08/21	Norway				
	938,699	12/16/60	United Kingdom				
	55-115327 (Abstract)	09/05/80	Japan				
	56-48128 (Abstract)	05/1/81	Japan				
	2065973A	07/01/81	United Kingdom				
	0080729 (Abstract)	05/20/82	Japan				
	57-208146 (Abstract)	12/21/82	Japan				
	02294027A	05/12/90	Japan				
	0 399 662 A2	11/28/90	European				
	WO 00/67298	11/09/00	PCT				

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Sf	J. Lue, "Arc Annealing of BF ₂ Implanted Silicon by a Short Pulse Flash Lamp," Appl. Phys. Lett., Volume 36, No. 1, pp. 73-76, dated January 1, 1980.
	M. Lefrancois and D. Camm, "Temperature Uniformity During Impulse TM Anneal," 8 th International Conference on Advanced Thermal Processing of Semiconductors, RTP 2000, pp. 1-6, dated September 20-22, 2000.
	A.T. Fiory, K.K. Bourdelle, P.K. roy and S.P. McCoy, "Spike Annealing of Implanted PMOS Gates," Proc. of RTP 2000 Conference, pp. 1-8, dated September 20-22, 2000.
	D.M. Camm and B. Lojek, "High Power Arc Lamp RTP System for High Temperature Annealing Applications," 2 nd International Rapid Thermal Conference, pp. 1-7, (1994).
	A.T. Fiory, K.K. Bourdelle, M.E. Lefrancois, D.M. Camm and A. Agarwal, "Electrical Measurements of Annealed Boron Implants for Shallow Junctions," Advances in Rapid Thermal Processing, Volume 99-10, pp. 133-140, (1999).
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Sf	A.R. Lunde, "Nasa Tech Brief," B75-1008, Lewis Research Center, dated April 1975.
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	N.S. Kapany, J.A. Eyer and R.E. Keim, "Fiber Optics. Part II. Image Transfer on Static and Dynamic Scanning with Fiber Bundles," Journal of the Optical Society of America, Volume 47, No. 5, pp. 423-427, dated May 1957.
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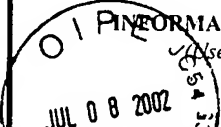
EXAMINER	Shauntina Fague	DATE CONSIDERED	3/7/04
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANTS Camm, et al.	RECEIVED MAY 2 2 2002 TECHNOLOGY CENTER R3700
(USE SEVERAL SHEETS IF NECESSARY)		EXPIRATION DATE December 4, 2001	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>gdy</i>	D. E. Williamson, "Cone Channel Condenser Optics," Journal of the Optical Society of America, Volume 42, No. 10, pp. 712-715, dated October 1952.
	R.L. Cohen, J.S. Williams, L.C. Feldman and K.W. West, Thermally Assisted Flash Annealing of Silicon and Germanium, Bell Laboratories, Murray Hill, New Jersey, pp. 1-4.
	R.J. von Gutfeld, "Crystallization of Silicon for Solar Cell Applications," IBM Technical Disclosure, Volume 19, IBM Corp., pp. 3955-3956, dated March 1977.
	T.O. Sedgwick, "Short Time Annealing," J. Electrochem. Soc., Volume 130, No. 2, pp. 484-492, dated February 1983.
	P. S. Burggraaf, "Rapid Wafer Heating: Status 1983," Semiconductor International, pp. 69-74, dated December 1983.
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	J. C. Gelpy and P. O. Stump, "Rapid Optical Annealing Using the Water-Wall DC Arc Lamp," Microelectronic Manufacturing and Testing, pp. 22-24, dated August 1983.
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	R.A. Powell and R.T. Fulks, "Annealing of Implantation Damage in Integrated-Circuit Devices Using an Incoherent Light Source," American Vacuum Society, pp. 32-36, dated January 1982.
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	J.H. Myer, "Zoomable Kaleidoscopic Mirror Tunnel," Applied Optics, Volume 10, No. 9, pp. 2179-2182, dated September 1971.
	"RTP-800 Rapid Thermal Processor," Extron Division Semiconductor Equipment Group, Varian, pp. 1-6, dated December 1985.
	K. Nishiyama, M. Arai and N. Watanabe, "Radiation Annealing of Boron-Implanted Silicon with a Halogen Lamp," Japanese Journal of Applied Physics, Volume 19, No. 10, pp. L563-L566, dated October 1980.
	M. Current and A. Yee, "Ion Implantation and Rapid Annealing of 125 mm Wafers," Solid State Technology, pp. 197-202, dated October 1983.
	D.J. Lischner and G.K. Celler, "Rapid Large Area Annealing of Ion-Implanted Si with Incoherent Light," Laser and Electron-Beam Interactions with Solids, Elsevier Science Publishing Company, Inc., pp. 751-758, (1982).
	J.C. C. Fan, B.-T. Tsaur and M.W. Geis, "Transient Heating with Graphite Heaters for Semiconductor Processing," Laser and Electron-Beam Interactions with Solids, Elsevier Science Publishing Company, Inc., pp. 751-758 (1982).
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	H.A. Bomke, H.L. Berkowitz, M. Harmatz, S. Kronenberg and R. Lux, "Annealing of Ion-Implanted Silicon by an Incoherent Light Pulse," Appl. Phys. Lett., Volume 33, No. 11, pp. 955-957, dated December 1, 1978.
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<i>gdy</i>	R.E. Sheets, "Automatic Cassette to Cassette Radiant Impulse Processor," Nuclear Instruments and Methods in Physics Research, Amsterdam, Elsevier Science Publishers B.V., pp. 219 - 223 (1985).

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EXAMINER <i>Sharon L. Fugua</i>	DATE CONSIDERED <i>3/7/04</i>
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	Atty. Docket No. FETHE24.001CP1 (47753-Scip)	Serial No. 10/005,186
	Applicant(s) David Malcolm Camm; J. Kiefer Elliott	
	Filing Date December 4, 2001	Group 3742

U.S. PATENT DOCUMENTS

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

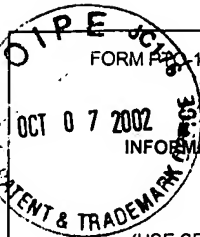
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
Self	AA	0 598 409	May 25/94	EP	—	—		

OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

Self	International Search Report for PCT/CA01/01706 (2 pages).
EXAMINER	Shacolina Fagua
	DATE CONSIDERED 3/6/04

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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<i>SH</i>	5,561,735	10/01/96	Camm	1	1	
<i>SH</i>	6,303,411	10/16/01	Camm, et al.	1	1	

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						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

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EXAMINER: <i>Shavontina Lague</i>	DATE CONSIDERED: <i>3/6/04</i>
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						YES	NO

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

<i>ST</i>	Tillmann, et al. "Processing of 200 and 300 mm Wafers in an Advanced Rapid Thermal Processing System," Proc RTP 1998, 6 th International Conference on Advanced Thermal Processing of Semiconductors, Kyoto, Japan, 1998, pp. 62-63.

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